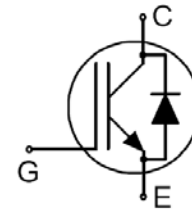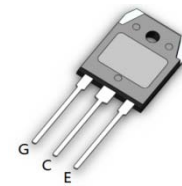# 1350V , 25A , Trench-FS IGBT

Features

- Advanced Trench+FS (Field Stop) IGBT technology
- Low Collector-Emitter Saturation voltage, typical data is 1.9V @ 25A.
- Easy parallel switching capability due to positive Temperature coefficient in Vce.
- 10uS short-circuit
- Fast switching
- High input impedance
- Pb- Free product

Schematic Diagram

TO3PN

Applications

- Power switch circuit of induction cooker.

Electrical characteristics(TJ = 25°C unless otherwise noted)							
Symbol	Parameter	Test conditions	Units	Min.	Typ.	Max.
$V_{(BR)CES}$	Collector - Emitter breakdown voltage	V_{GE} = 0V, I_D = 0.5mA	V	1350	—	—
$V_{CE(sat)}$	Collector-Emitter Saturation voltage	V_{GE}=15V, I_C=25A,T_C=25°C	V	—	1.9	2.1
		V_{GE}=15V, I_C=25A,T_C=125°C	V	—	2.05	—
$V_{GE(th)}$	Gate threshold voltage	V_{GE}= V_{CE}, I_D = 0.4mA	V	4.0	5.2	6.5
V_F	Diode Forward voltage	Ic=25A	V	—	2.5	2.9
I_{GES}	Gate to Emitter Forward Leakage	Vge=+30V	nA	—	—	200
I_{GESR}	Gate to Emitter reverse Leakage	Vge=-30V		-200	—	—
I_{CES}	Zero gate voltage collector current	V_{CE} =1350V	uA	—	—	100

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